

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A transistor, comprising:

a monocrystalline semiconductor layer including a channel region, a lightly doped region, and a heavily doped region, the monocrystalline semiconductor layer having a surface, a side extending substantially perpendicular to the surface, and a shoulder portion disposed where the surface and the side intersect; and

a gate insulating film provided over the monocrystalline semiconductor layer, the gate insulating film ~~having:~~ having a total thickness set in a range of 60nm to 80nm, and including:

a thermal oxide film formed on the monocrystalline semiconductor layer, ~~layer to a thickness in a range of 5nm to 50nm,~~ the thermal oxide film being thinner at a portion corresponding to the shoulder portion of the monocrystalline semiconductor layer than that at other portions; and

at least one vapor-deposited insulating film formed on the ~~thermal~~ thermal oxide film, the at least one vapor-deposited insulating film covering an area including at least the channel region, the lightly doped region, and the heavily doped region of the monocrystalline semiconductor layer, the at least one vapor-deposited insulating film having a thickness at the shoulder portion of the monocrystalline semiconductor layer that is substantially equal to that at other portions.

2. (Original) The transistor according to claim 1, the monocrystalline semiconductor layer being made of monocrystalline silicon.

3. (Original) The transistor according to claim 1, the monocrystalline semiconductor layer being a mesa type.

4. (Original) The transistor according to claim 1, the monocrystalline semiconductor layer having a thickness of 15 to 60 nm.
- 5-7. (Canceled)
8. (Original) An electro-optical device, comprising:  
a transistor according to claim 1.
9. (Original) An electro-optical device in which an electro-optical material is interposed between a pair of substrates facing each other,  
a transistor according to claim 1 being provided as a switching element in a display area.
10. (Original) A semiconductor device, comprising:  
a transistor according to claim 1.
11. (Original) An electronic apparatus, comprising:  
an electro-optical device according to claim 8.
- 12-14. (Canceled)
15. (Original) An electronic apparatus, comprising:  
a semiconductor device according to claim 10.
16. (Previously Presented) The transistor according to claim 1, further comprising:  
a capacitor line, the monocrystalline semiconductor layer further having a storage capacitor electrode portion that includes the shoulder portion, the thermal oxide film and the vapor-deposited insulating film being interposed between the capacitor line and the storage capacitor electrode portion and serving as a dielectric.
17. (Canceled)